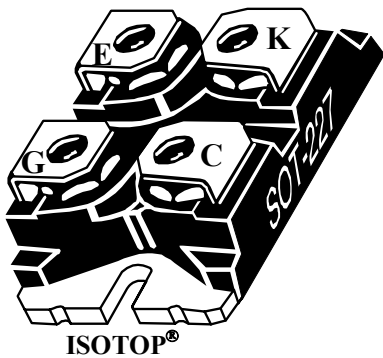
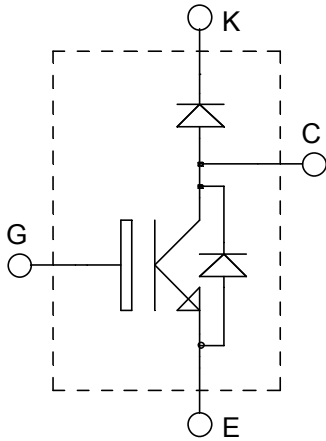


**ISOTOP® Boost chopper
NPT IGBT**

**$V_{CES} = 600V$
 $I_C = 50A @ T_c = 90^\circ C$**



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- Non Punch Through (NPT) THUNDERBOLT IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 100 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- ISOTOP® Package (SOT-227)
- Very low stray inductance
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_{C1}	Continuous Collector Current	$T_C = 25^\circ C$	A
I_{C2}		$T_C = 90^\circ C$	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	160
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	277
I_{LM}	RBSOA clamped Inductive load Current $R_G=11\Omega$	$T_C = 25^\circ C$	100
I_{FAV}	Maximum Average Forward Current	Duty cycle=0.5 $T_C = 80^\circ C$	30
I_{FRMS}	RMS Forward Current (Square wave, 50% duty)		39

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
BV_{CES}	Collector - Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	600			V
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V$			40	μA
		$V_{CE} = 600V$			1000	
$V_{CE(on)}$	Collector Emitter on Voltage	$V_{GE} = 15V$		2.1	2.7	V
		$I_C = 50A$		2.2	2.8	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 700\mu A$	4.5	5.5	6.5	V
I_{GES}	Gate - Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$			± 100	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V$		2250		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		255		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		155		
Q_g	Total gate Charge	$V_{GS} = 15V$		175		nC
Q_{ge}	Gate - Emitter Charge	$V_{Bus} = 300V$		18		
Q_{gc}	Gate - Collector Charge	$I_C = 50A$		100		
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching (25°C)		29		ns
T_r	Rise Time	$V_{GE} = 15V$		118		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 300V$		150		
T_f	Fall Time	$I_C = 50A$		190		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		30		ns
T_r	Rise Time	$V_{GE} = 15V$		80		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$		240		
T_f	Fall Time	$I_C = 50A$		43		
E_{ts}	Total switching Losses	$R_G = 10\Omega$		3.6		mJ
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C)		28		ns
T_r	Rise Time	$V_{GE} = 15V$		75		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 400V$		265		
T_f	Fall Time	$I_C = 50A$		185		
E_{on}	Turn-on Switching Energy	$R_G = 10\Omega$		1.8		mJ
E_{off}	Turn-off Switching Energy			2.4		
E_{ts}	Total switching Losses			4.2		

Diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V _F	Diode Forward Voltage	I _F = 30A			1.6	1.8	V
		I _F = 60A			1.9		
		I _F = 30A	T _j = 125°C		1.4		
I _{RM}	Maximum Reverse Leakage Current	V _R = 600V	T _j = 25°C			250	μA
		V _R = 600V	T _j = 125°C			500	
C _T	Junction Capacitance	V _R = 200V			44		pF
t _{rr}	Reverse Recovery Time	I _F = 1A, V _R = 30V	T _j = 25°C		23		ns
	Reverse Recovery Time		T _j = 25°C		85		
			T _j = 125°C		160		
I _{RRM}	Maximum Reverse Recovery Current	I _F = 30A V _R = 400V di/dt = 200A/μs	T _j = 25°C		4		A
			T _j = 125°C		8		
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		130		nC
			T _j = 125°C		700		
t _{rr}	Reverse Recovery Time	I _F = 30A	T _j = 125°C		70		ns
Q _{rr}	Reverse Recovery Charge	V _R = 400V			1300		nC
I _{RRM}	Maximum Reverse Recovery Current	di/dt = 1000A/μs			30		A

Thermal and package characteristics

<i>Symbol</i>	<i>Characteristic</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R _{thJC}	Junction to Case	IGBT			0.45	°C/W
		Diode			1.21	
R _{thJA}	Junction to Ambient (IGBT & Diode)				20	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz		2500			V
T _J , T _{STG}	Storage Temperature Range		-55		150	°C
T _L	Max Lead Temp for Soldering: 0.063" from case for 10 sec				300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)				1.5	N.m
Wt	Package Weight			29.2		g

Typical IGBT Performance Curve

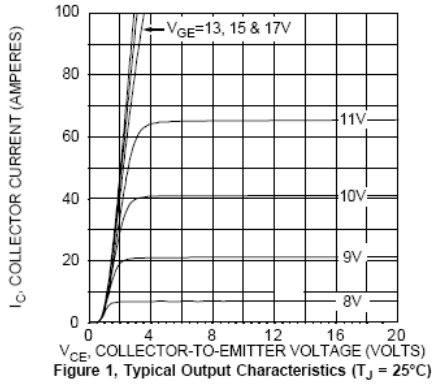


Figure 1, Typical Output Characteristics ($T_J = 25^\circ\text{C}$)

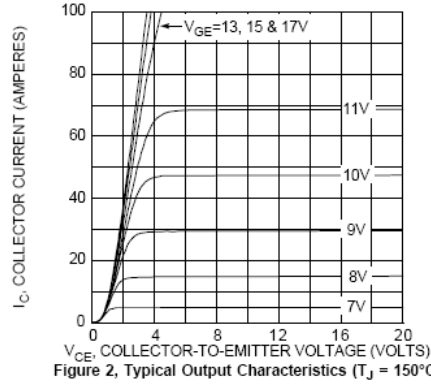


Figure 2, Typical Output Characteristics ($T_J = 150^\circ\text{C}$)

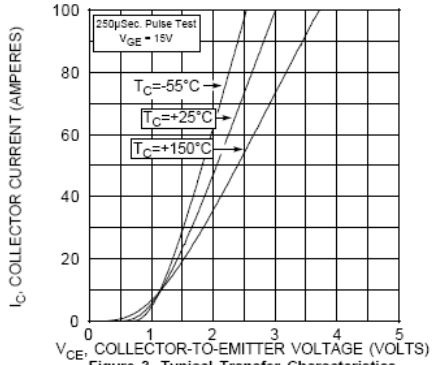


Figure 3, Typical Transfer Characteristics

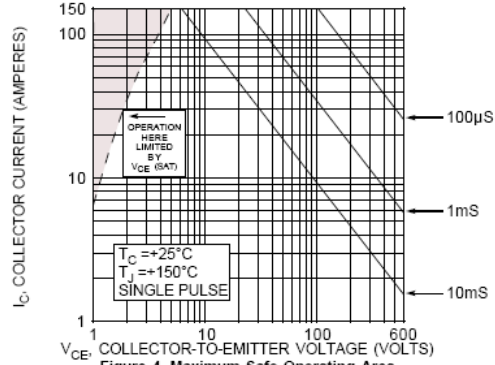


Figure 4, Maximum Safe Operating Area

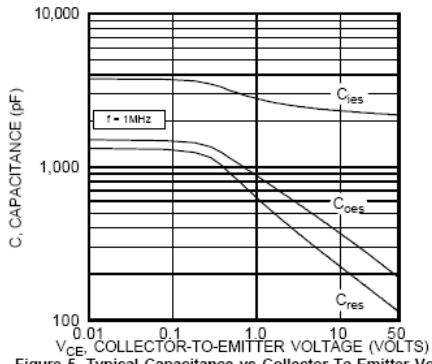


Figure 5, Typical Capacitance vs Collector-To-Emitter Voltage

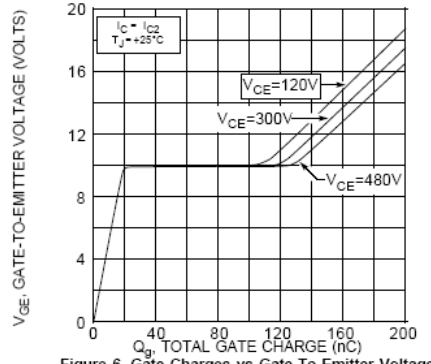


Figure 6, Gate Charges vs Gate-To-Emitter Voltage

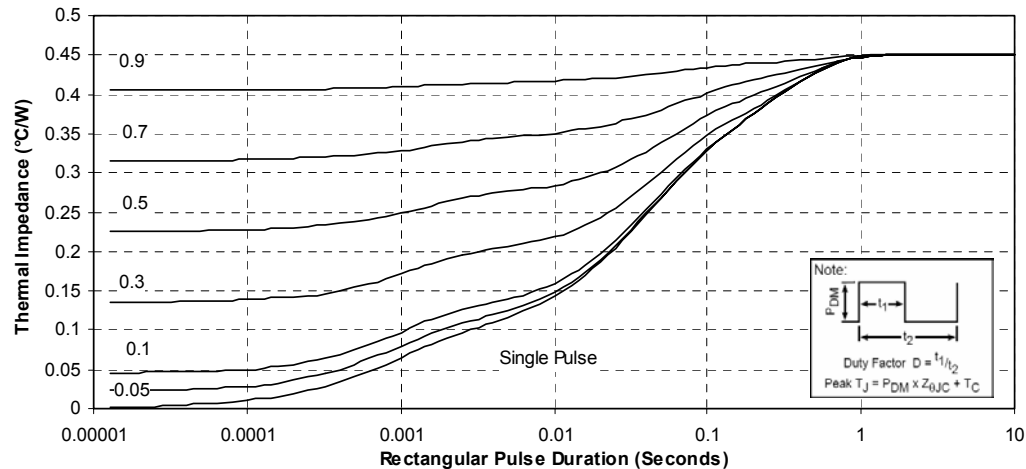


Figure 7, Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration

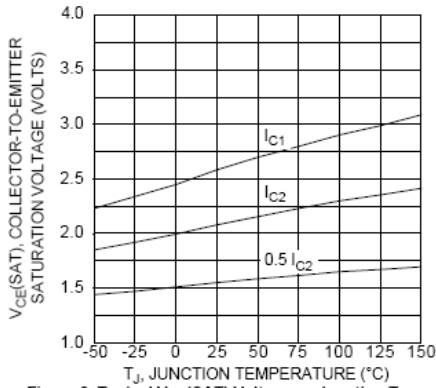


Figure 8, Typical $V_{CE(SAT)}$ Voltage vs Junction Temperature

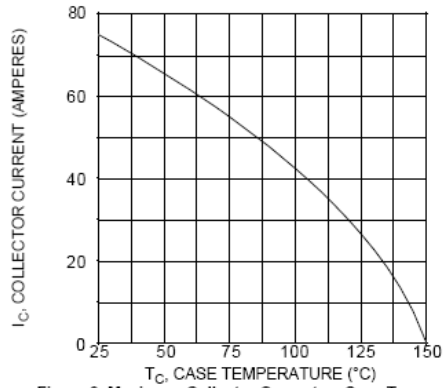


Figure 9, Maximum Collector Current vs Case Temperature

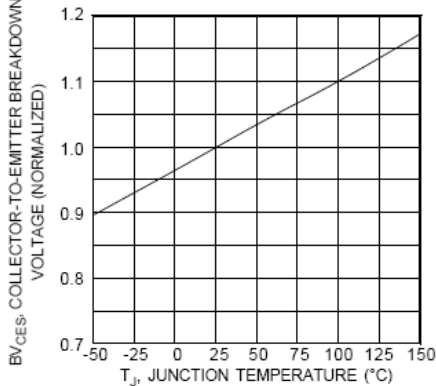


Figure 10, Breakdown Voltage vs Junction Temperature

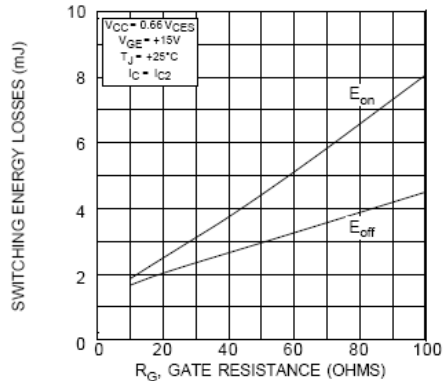


Figure 11, Typical Switching Energy Losses vs Gate Resistance

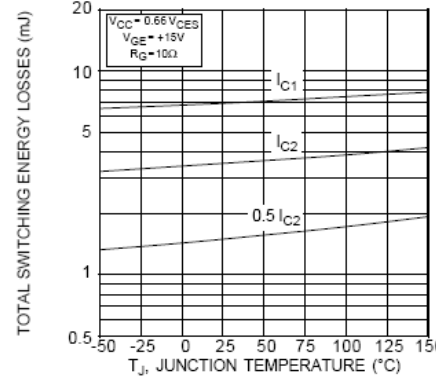


Figure 12, Typical Switching Energy Losses vs. Junction Temperature

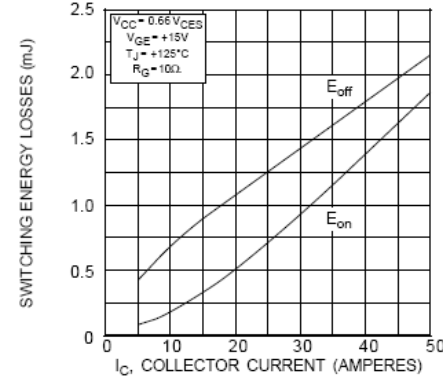


Figure 13, Typical Switching Energy Losses vs Collector Current

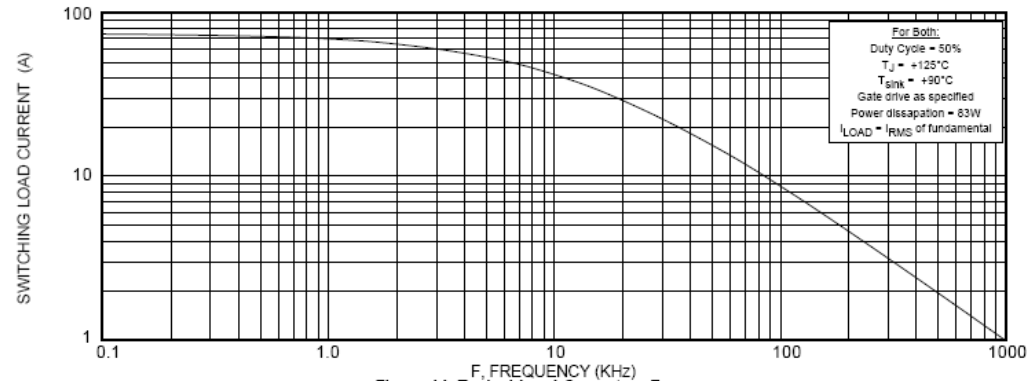


Figure 14, Typical Load Current vs Frequency

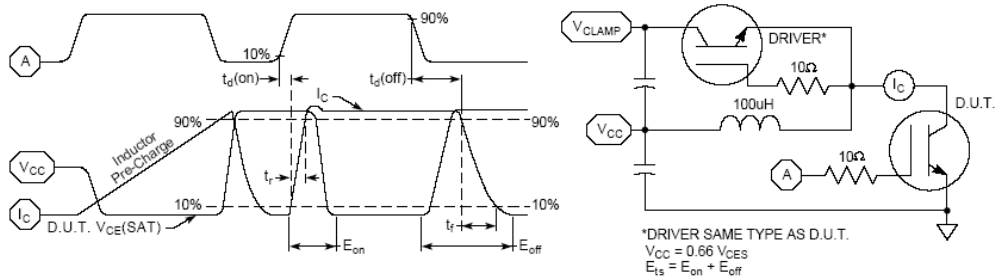


Figure 16, Switching Loss Test Circuit and Waveforms

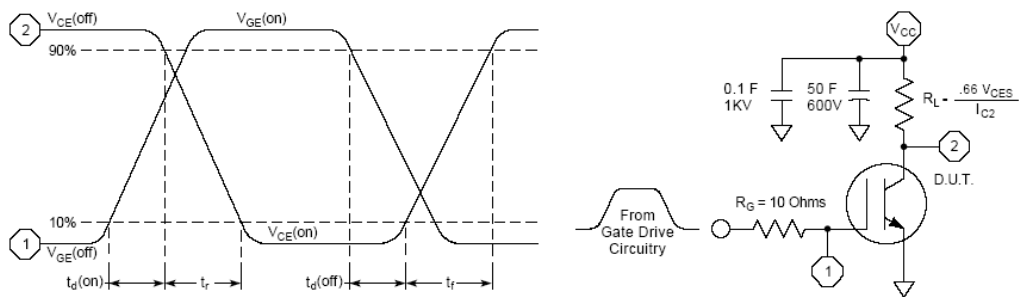


Figure 17, Resistive Switching Time Test Circuit and Waveforms

Typical Diode Performance Curve

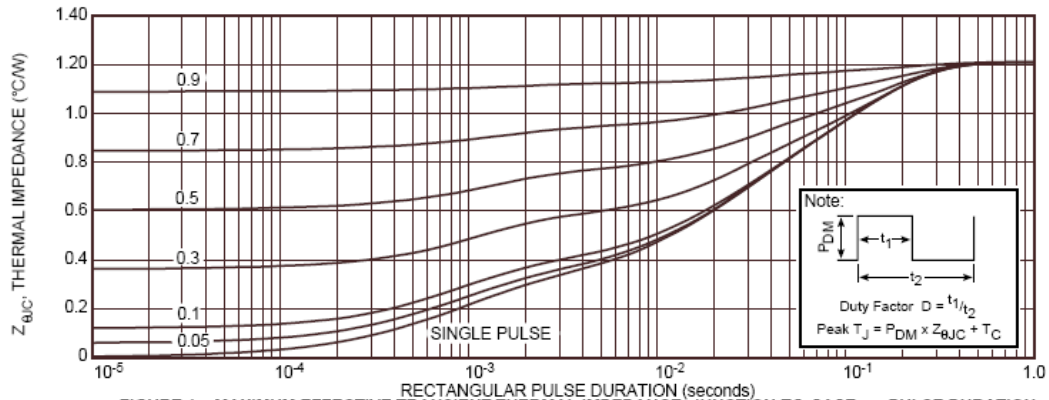


FIGURE 1a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

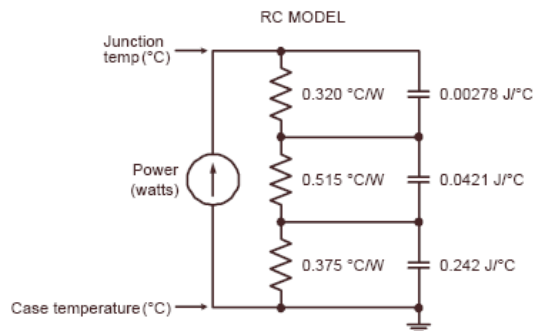


FIGURE 1b, TRANSIENT THERMAL IMPEDANCE MODEL

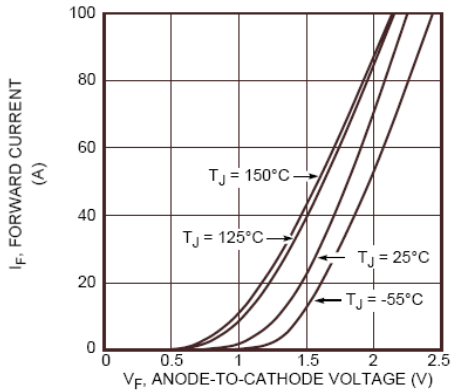


Figure 2. Forward Current vs. Forward Voltage

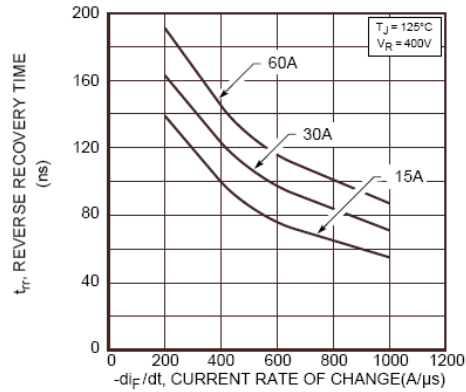


Figure 3. Reverse Recovery Time vs. Current Rate of Change

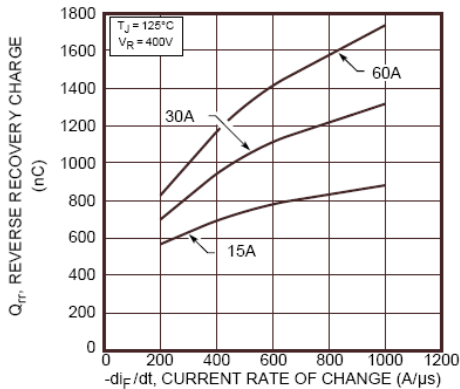


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

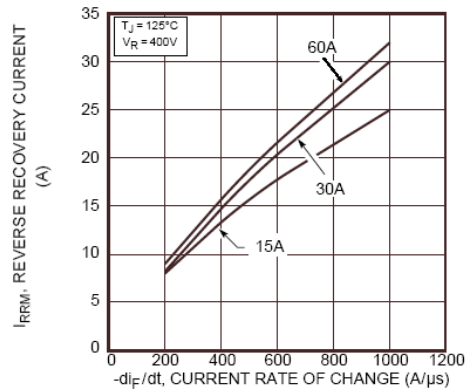


Figure 5. Reverse Recovery Current vs. Current Rate of Change

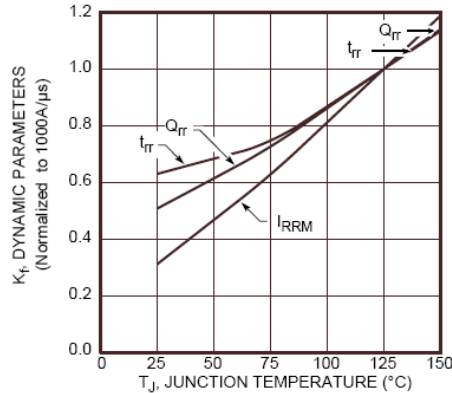


Figure 6. Dynamic Parameters vs. Junction Temperature

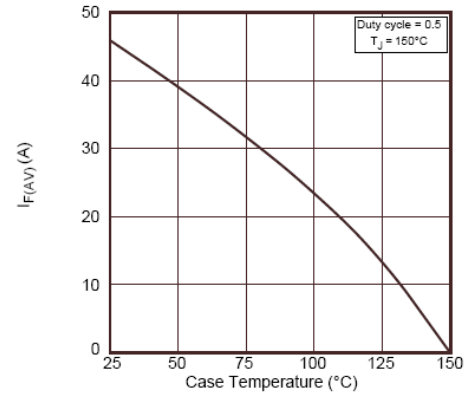


Figure 7. Maximum Average Forward Current vs. Case Temperature

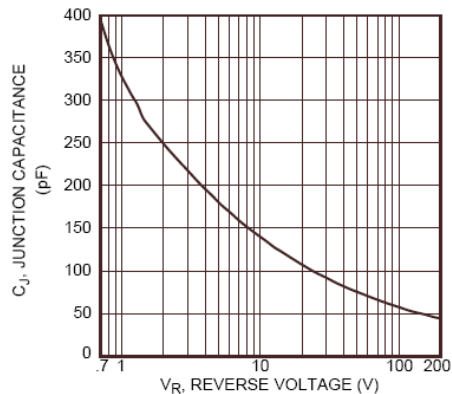


Figure 8. Junction Capacitance vs. Reverse Voltage

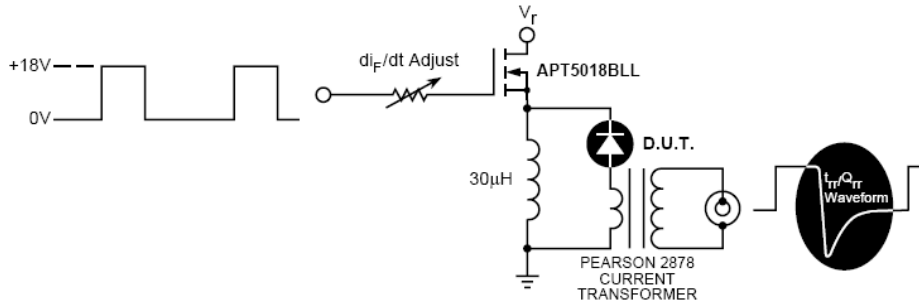


Figure 9. Diode Test Circuit

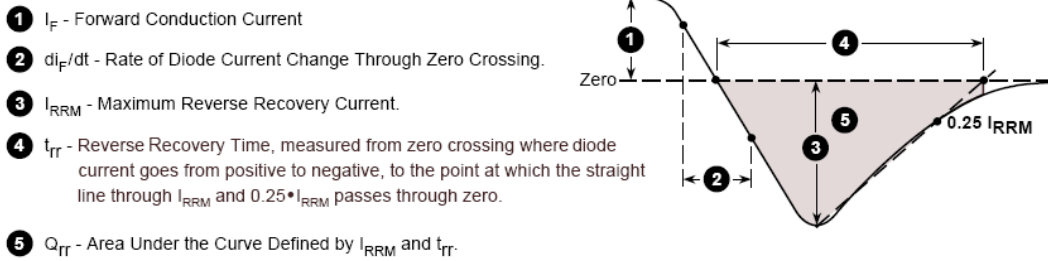
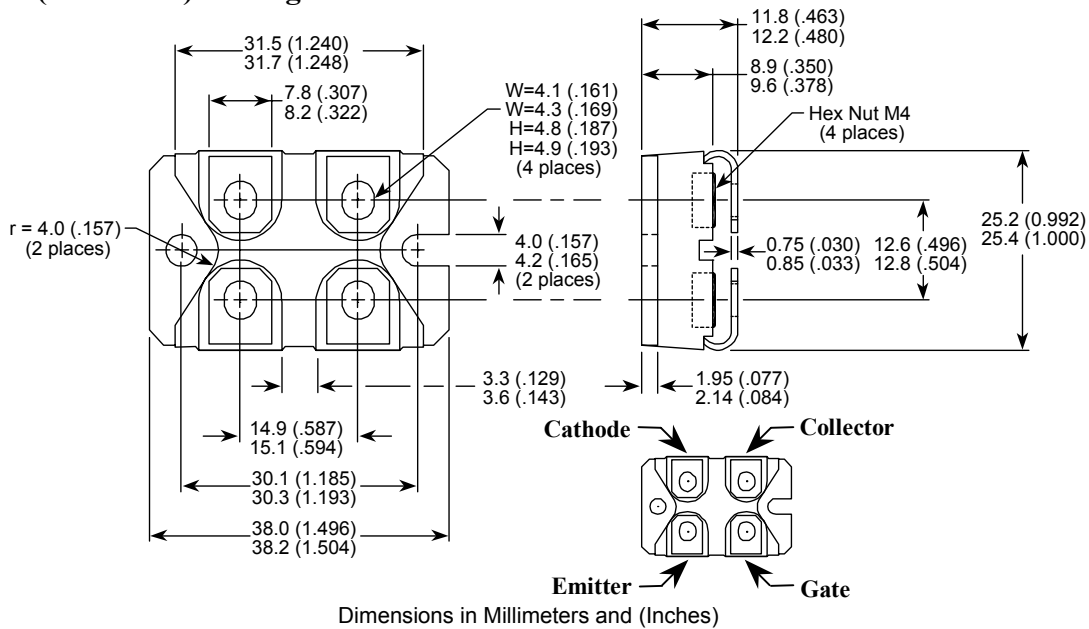


Figure 10. Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



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APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.